

**WHAT IS CLAIMED IS:**

1           1.     A projection exposure apparatus for projecting a pattern image  
2     formed on a mask onto a photosensitive substrate through a projection optical  
3     system to form a projected image thereon, the projection exposure apparatus  
4     comprising:

5                 a substrate position detector that detects a position of a registration  
6     mark formed on the substrate;

7                 an imagery characteristic correction mechanism coupled with the  
8     projection optical system that drives the projection optical system to correct an  
9     imagery characteristic of the projection optical system;

10                an image-forming displacement detector communicating with said  
11     imagery characteristic correction mechanism, said image-forming displacement  
12     detector determining a displacement amount of an image-forming position of the  
13     projected image in accordance with a driven amount of the projection optical  
14     system by said imagery characteristic correction mechanism; and

15                an alignment signal processor communicating with said substrate  
16     position detector and said image-forming displacement detector, said alignment  
17     signal processor correcting the detection result of the substrate position detector  
18     based on the displacement amount of the image-forming position obtained by the  
19     image-forming displacement detector.

1           2.     The projection exposure apparatus of claim 1, further comprising a  
2     memory storing a relation between the driven amount of the projection optical  
3     system by said imagery characteristic correction mechanism and the displacement  
4     amount of the image-forming position, said image-forming displacement detector  
5     communicating with said memory.

1           3.     The projection exposure apparatus of claim 2, wherein said  
2     projection optical system comprises the mask and at least one optical element that  
3     projects the pattern image formed on the mask onto the photosensitive substrate,  
4     said imagery characteristic correction mechanism having a driving device coupled  
5     to the mask and said optical element, said driving device driving or tilting at least  
6     one of the mask or said optical element along an optical axis direction of the  
7     projection optical system or with respect to a plane perpendicular to the optical  
8     axis.

1           4.     The projection exposure apparatus of claim 2, further comprising a  
2     pressure adjustment mechanism communicating with said imagery characteristic  
3     correction mechanism, said projection optical system comprising at least two  
4     optical elements disposed along the optical axis, said optical elements defining a  
5     sealed space therebetween, wherein said imagery characteristic correction  
6     mechanism controls said gas pressure adjustment mechanism to change a gas  
7     pressure in said sealed space.

1           5.     The projection exposure apparatus of claim 1, wherein said  
2     projection optical system comprises the mask and at least one optical element that  
3     projects the pattern image formed on the mask onto the photosensitive substrate,  
4     said imagery characteristic correction mechanism having a driving device coupled  
5     to the mask and said optical element, said driving device driving or tilting at least  
6     one of the mask or said optical element along an optical axis direction of the  
7     projection optical system or with respect to a plane perpendicular to the optical  
8     axis.

1           6.     The projection exposure apparatus of claim 1, further comprising a  
2     pressure adjustment mechanism communicating with said imagery characteristic  
3     correction mechanism, said projection optical system comprising at least two

4 optical elements disposed along the optical axis, said optical elements defining a  
5 sealed space therebetween, wherein said imagery characteristic correction  
6 mechanism controls said gas pressure adjustment mechanism to change a gas  
7 pressure in said sealed space.

1 7. The projection exposure apparatus of claim 1, further comprising  
2 at least one displacement detector secured to the projection optical system and  
3 communicating with said image-forming displacement detector, said  
4 displacement detector detecting the driven amount of the projection optical  
5 system by said imagery characteristic correction mechanism.

1 8. The projection exposure apparatus of claim 1, further comprising  
2 an environmental sensor disposed adjacent the projection optical system and  
3 communicating with said imagery characteristic correction mechanism.

1 9. A projection exposure apparatus for projecting a pattern image of a  
2 mask through a projection optical system onto a photosensitive substrate to form  
3 a projected image thereon, the projection exposure apparatus comprising:  
4 a substrate position detector that detects a position of a registration  
5 mark formed on the substrate;  
6 an imagery characteristic correction mechanism coupled with the  
7 projection optical system that drives the projection optical system to correct an  
8 imagery characteristic of the projection optical system;  
9 a base-line amount measuring device that measures a distance  
10 between a detection center of said substrate position detector and a center of the  
11 projected image formed through the projection optical system, said distance  
12 defining a base-line amount; and  
13 an alignment signal processor communicating with said substrate  
14 position detector and said base-line amount measuring device, said alignment

15 signal processor correcting the detection result of the substrate position detector  
16 based on the base-line amount.

1 10. The projection exposure apparatus of claim 9, wherein said base-  
2 line amount measuring device comprises a reference plate disposed adjacent and  
3 substantially level with the photosensitive substrate, said reference plate including  
4 primary alignment marks corresponding to alignment marks on the mask.

1 11. The projection exposure apparatus of claim 10, wherein said  
2 reference plate includes a secondary alignment mark disposed adjacent said  
3 substrate position detector during initial alignment, said substrate position  
4 detector determining an offset amount in accordance with a distance between a  
5 center point between said primary alignment marks and said secondary alignment  
6 mark.

1 12. The projection exposure apparatus of claim 10, wherein said base-  
2 line amount measuring device further comprises a pair of mask alignment  
3 microscopes, said mask alignment microscopes being disposed adjacent the  
4 alignment marks on the mask for detecting the alignment marks on the mask.

1 13. A method of projecting a pattern image formed on a mask onto a  
2 photosensitive substrate through a projection optical system having an optical  
3 axis to form a projected image thereon, the method comprising:

4 (a) detecting with a substrate position detector a position of a  
5 registration mark formed on the substrate;

6 (b) driving the projection optical system to correct an imagery  
7 characteristic of the projection optical system;

8 (c) determining a displacement amount of an image-forming  
9 position of the projected image formed through the projection optical system in

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10 accordance with a driven amount of the projection optical system in step (a); and  
11 (d) correcting the detected position from step (a) based on the  
12 displacement amount.

1 14. The method of claim 13, wherein a memory stores a relation  
2 between the driven amount of the projection optical system and the displacement  
3 amount of the image-forming position, said step (c) being practiced by accessing  
4 the displacement amount stored in the memory in accordance with the driven  
5 amount.

1 15. The method of claim 14, wherein step (b) is practiced by driving or  
2 tilting at least one of the mask or an optical element of the projection optical  
3 system along an optical axis direction of the projection optical system or with  
4 respect to a plane perpendicular to the optical axis.

1 16. The method of claim 14, wherein step (b) is practiced by  
2 controlling a gas pressure in a space defined by optical elements of the projection  
3 optical system.

1 17. The method of claim 13, wherein step (b) is practiced by driving or  
2 tilting at least one of the mask or an optical element of the projection optical  
3 system along an optical axis direction of the projection optical system or with  
4 respect to a plane perpendicular to the optical axis.

1 18. The method of claim 13, wherein step (b) is practiced by  
2 controlling a gas pressure in a space defined by optical elements of the projection  
3 optical system.

1 19. The method of claim 13, wherein step (c) is practiced by, prior to  
2 step (b), measuring a distance between a detection center of the substrate position  
3 detector and a center of the projected image formed through the projection optical  
4 system defining a base-line amount, and after step (b), again measuring the base-  
5 line amount.

1 20. The method of claim 19, wherein a base-line amount measuring  
2 device for measuring the base-line amount includes a reference plate disposed  
3 adjacent and substantially level with the photosensitive substrate, the reference  
4 plate including primary alignment marks corresponding to alignment marks on  
5 the mask and a secondary alignment mark disposed adjacent the substrate position  
6 detector during initial alignment, wherein step (c) is further practiced by  
7 determining an offset amount in accordance with a distance between a center  
8 point between the primary alignment marks and the secondary alignment mark,  
9 and adding the offset amount to the base-line amount.

1 21. The method of claim 13, further comprising, prior to step (a) the  
2 step of (e) aligning the mask with respect to the projection optical system.

1 22. The method of claim 21, wherein step (e) is practiced by:  
2 (e1) detecting positions of projected images of at least two  
3 alignment marks formed on the mask, the alignment marks having a  
4 predetermined positional relationship with the pattern image;  
5 (e2) changing a magnification of the projection optical system;  
6 (e3) detecting the positions of the projected images after step (e2);  
7 and  
8 (e4) adjusting the mask position based on the positions of the  
9 projected images determined in steps (e1) and (e3).

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1           23.    The method of claim 22, further comprising the step of repeating  
2 steps (e1) through (e4) until a center of the pattern image projected onto the  
3 photosensitive substrate is aligned with the optical axis even after the  
4 magnification of the projection optical system has been changed.

1           24.    The method of claim 22, comprising the steps of replacing the  
2 mask with a second mask and positioning the second mask in the same position as  
3 the first mask based on mask position information obtained in step (e4).

1           25.    The method of claim 24, wherein the mask position information is  
2 a position of a reference mark corresponding to the mask position adjusted in step  
3 (e4).

1           26.    The method of claim 24, wherein the mask position information is  
2 information supplied from a mask position adjusting mechanism during the mask  
3 adjustment performed in step (e4).

1           27.    A mask alignment method for aligning a mask with respect to a  
2 projection optical system having an optical axis prior to transferring a pattern  
3 image of the mask onto a photosensitive substrate through the projection optical  
4 system, the method comprising:

5                   (a) detecting positions of projected images of at least two  
6 alignment marks formed on the mask, the alignment marks having a  
7 predetermined positional relationship with the pattern image;

8                   (b) changing a magnification of the projection optical system;

9                   (c) detecting the positions of the projected images after step (e2);

10          and

11                   (d) adjusting the mask position based on the positions of the  
12 projected images determined in steps (a) and (c).

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1           28.    The method of claim 27, further comprising the step of repeating  
2           steps (a) through (d) until a center of the pattern image projected onto the  
3           photosensitive substrate is aligned with the optical axis even after the  
4           magnification of the projection optical system has been changed.

1           29.    The method of claim 27, comprising the steps of replacing the  
2           mask with a second mask and positioning the second mask in the same position as  
3           the first mask based on mask position information obtained in step (d).

1           30.    The method of claim 29, wherein the mask position information is  
2           a position of a reference mark corresponding to the mask position adjusted in step  
3           (d).

1           31.    The method of claim 29, wherein the mask position information is  
2           information supplied from a mask position adjusting mechanism during the mask  
3           adjustment performed in step (d).

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